

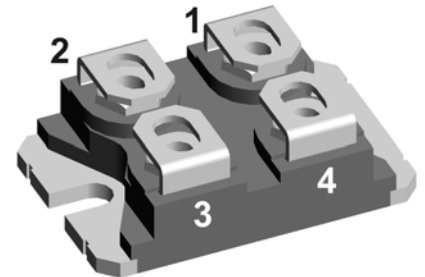
HiPerFRED

$$\begin{aligned}
 V_{RRM} &= 1200V \\
 I_{FAV} &= 2 \times 60A \\
 t_{rr} &= 35ns
 \end{aligned}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Parallel legs

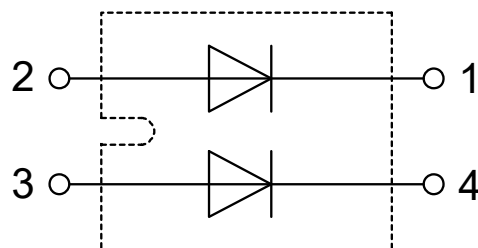
Part number

DSEP2x61-12B



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

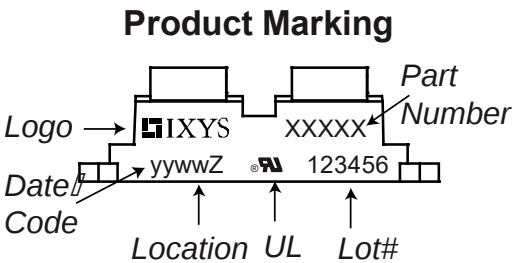
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Fast Diode				Ratings					
Symbol	Definition	Conditions		min.	typ.	max.	Unit		
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V		
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V		
I_R	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			200	μA		
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1	mA		
V_F	forward voltage drop	$I_F = 60\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2,90	V		
		$I_F = 120\text{ A}$				3,50	V		
		$I_F = 60\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			2,00	V		
		$I_F = 120\text{ A}$				2,60	V		
I_{FAV}	average forward current	$T_C = 80^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			60	A		
		rectangular d = 0.5							
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		1,10	V		
r_F	slope resistance					12	m Ω		
R_{thJC}	thermal resistance junction to case					0,6	K/W		
R_{thCH}	thermal resistance case to heatsink				0,1		K/W		
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				200	W		
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^{\circ}\text{C}$		800	A		
C_J	junction capacitance	$V_R = 600\text{ V}$ f = 1 MHz		$T_{VJ} = 25^{\circ}\text{C}$		48	pF		
I_{RM}	max. reverse recovery current	} $I_F = 60\text{ A}; V_R = 600\text{ V}$ -di _F /dt = 200 A/μs		$T_{VJ} = 25^{\circ}\text{C}$		11	A		
				$T_{VJ} = 125^{\circ}\text{C}$		17	A		
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		70	ns		
				$T_{VJ} = 125^{\circ}\text{C}$		210	ns		

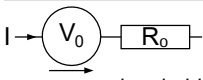
advanced

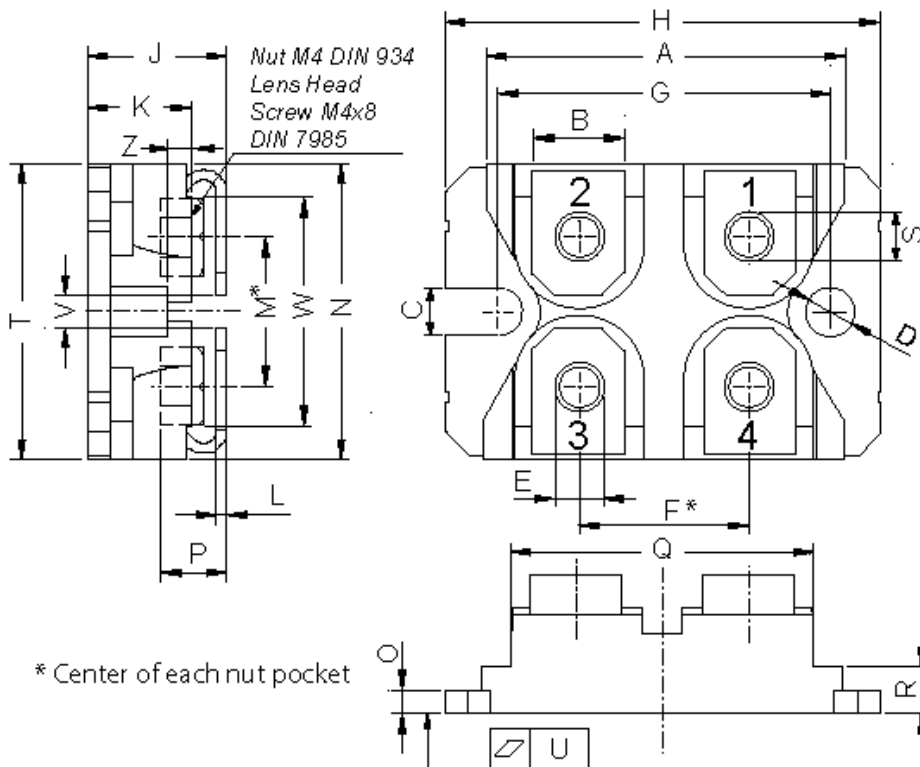
Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		150	°C
Weight					30		g
M _D	mounting torque			1,1		1,5	Nm
M _T	terminal torque			1,1		1,5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	10,5	3,2			mm
d _{Spb/Apb}		terminal to backside	8,6	6,8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000		V
		t = 1 minute			2500		V



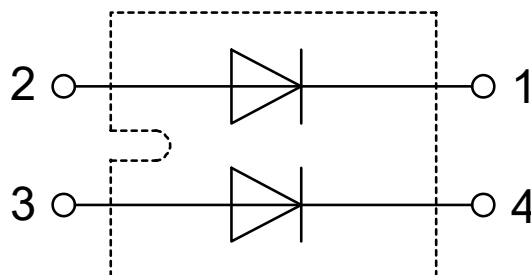
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x61-12B	DSEP2x61-12B	Tube	10	520842

Similar Part	Package	Voltage class
DSEP2x61-12A	SOT-227B (minibloc)	1200

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}\text{C}$
	$V_{0\text{ max}}$	threshold voltage	1,1	V
	$R_{0\text{ max}}$	slope resistance *	10	mΩ

Outlines SOT-227B (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



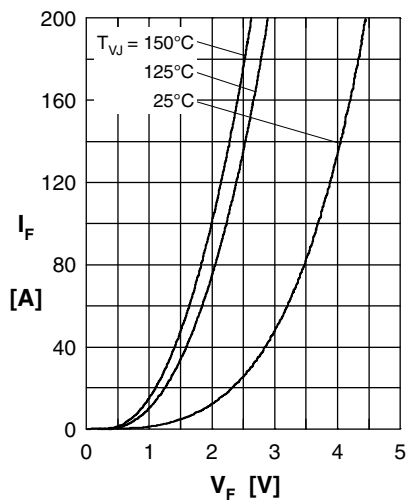
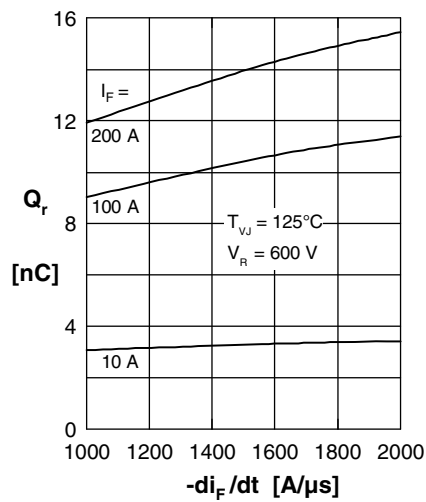
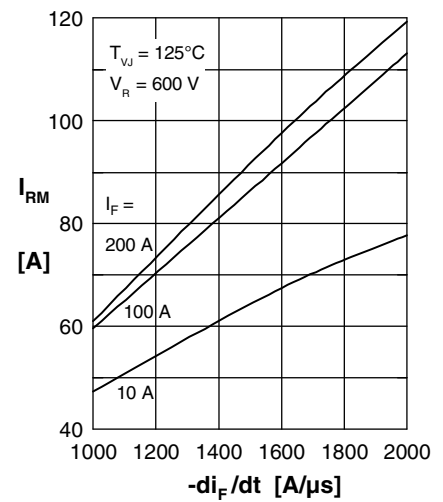
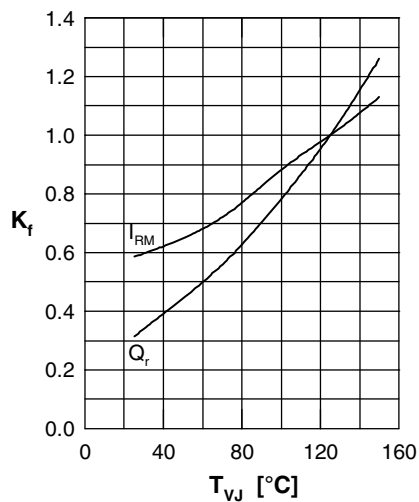
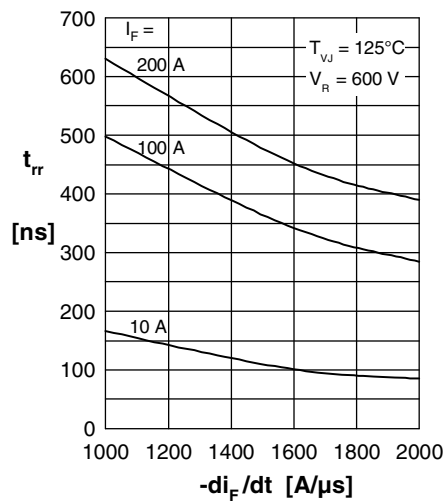
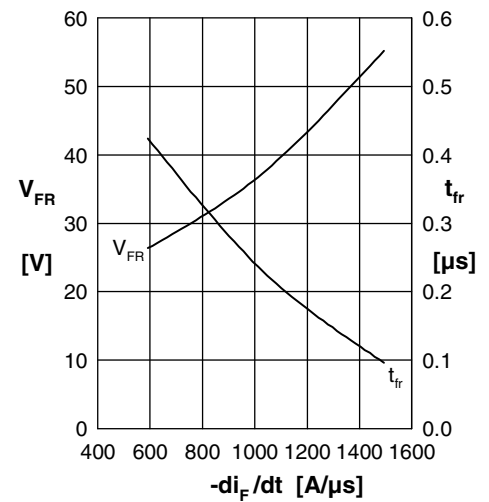
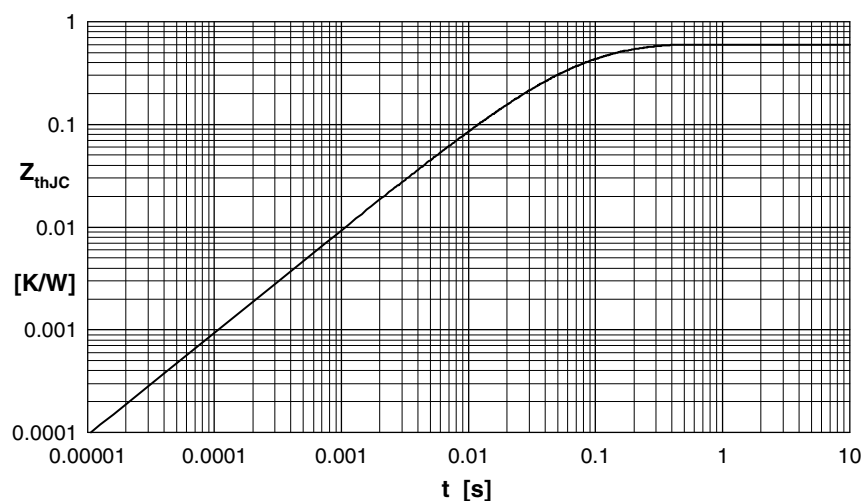
Fast Diode

 Fig. 1 Forward current I_F versus V_F

 Fig. 2 Typ. reverse recov.charge Q_r versus $-di_F/dt$

 Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt


Fig. 7 Transient thermal resistance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.212	0.0055
2	0.248	0.0092
3	0.063	0.0007
4	0.077	0.0391